

***Remarks***

Applicants thank the Examiner for his careful consideration of this application. Reconsideration of this application is now respectfully requested in view of the amendments above and the following remarks.

Claims 1-14 and 25-33 are now pending in the application, with Claims 1 and 25 being the independent claims. Claim 1 has been amended, and new Claims 25-33 have been added. Claims 15-24 have been cancelled without prejudice to pursue their subject matter in one or more future applications. It is noted that new Claims 25-33 are supported at least by the claims as originally filed.

Applicants gratefully acknowledge the indication of allowable subject matter in Claims 4, 6, 7, and 9-14 at Page 4 of the Office Action. Applicants have opted not to amend these claims, at this time, to include the limitations of the claims from which they depend.

At Pages 2-3, the Office Action rejects Claims 1-3 and 8 under 35 U.S.C. § 102(b) as being anticipated by Kanazawa et al. (U.S. Patent No. 5,920,089). At Pages 3-4, the Office Action rejects Claims 1-3 and 5 under 35 U.S.C. § 102(b) as being anticipated by Hsu et al. (U.S. Patent No. 5,818,085). Applicants respectfully traverse these rejections for the following reasons.

Claim 1, as amended, recites "a resistance region disposed in the layer between the first transistor and the body contact region to substantially isolate the first transistor from the body

contact region, the resistance region having a resistivity higher than a resistivity of the layer." In contrast, Kanazawa et al., noting Fig. 5B, col. 8, lines 55-65, and col. 9, lines 41-55, for example, discloses a common high-voltage power supply ( $V_{DDH}$ ) being coupled to the bodies of all regions. Hsu et al., noting, for example, col. 3, lines 44-46, discloses a single body contact formed to provide a common body contact for all transistors (i.e., all regions). Therefore, neither Kanazawa et al. nor Hsu et al. discloses a device in which a resistance region provides substantial isolation between a first transistor and a body contact region, as claimed in Claim 1.

In view of this, it is respectfully submitted that Claim 1 and Claims 2-14, which depend from Claim 1, are allowable over the cited prior art, for at least these reasons.

Furthermore, new Claim 25 recites "a layer of a first conductivity type formed directly on a semiconductor substrate." In contrast, Kanazawa et al., noting, for example, the figures (e.g., Fig. 5C), discloses transistors formed in wells in a semiconductor substrate, rather than in a layer formed on a semiconductor substrate. Hsu et al., noting, e.g., the figures and col. 2, lines 1-2, 11-13, and 56-67, discloses a silicon-on-insulator device, where transistors (e.g., in Fig. 6) are formed in a semiconductor layer deposited on an insulation layer (an oxide layer). Hence, neither Kanazawa et al. nor Hsu et al. discloses the claimed layer.

Consequently, it is respectfully submitted that new Claim 25 and Claims 26-33, which depend from Claim 25, are allowable over the cited prior art, for at least these reasons.

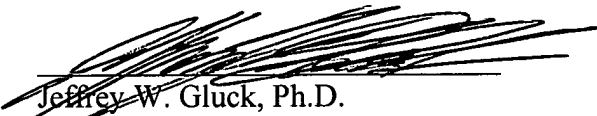
***Conclusion***

All of the stated grounds of objection and rejection have been properly traversed, accommodated, or rendered moot. Applicants, therefore, respectfully request that the Examiner reconsider all presently outstanding objections and rejections and that they be withdrawn. Applicants believe that a full and complete reply has been made to the outstanding Office Action and, as such, the present application is in condition for allowance. If the Examiner believes, for any reason, that personal communication will expedite prosecution of this application, the Examiner is hereby invited to telephone the undersigned at the number provided.

Prompt and favorable consideration of this Amendment and Reply is respectfully requested.

Respectfully submitted,

Date: December 8, 2004



Jeffrey W. Gluck, Ph.D.  
Registration No. 44,457  
VENABLE LLP  
P.O. Box 34385  
Washington, D.C. 20043-9998  
Telephone: (202) 344-4000  
Direct Dial: (202) 344-8017  
Telefax: (202) 344-8300